

### Is Now Part of



# ON Semiconductor®

# To learn more about ON Semiconductor, please visit our website at www.onsemi.com

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (\_), the underscore (\_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (\_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at <a href="www.onsemi.com">www.onsemi.com</a>. Please email any questions regarding the system integration to Fairchild <a href="guestions@onsemi.com">guestions@onsemi.com</a>.

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any EDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officer



September 2016

### FNB81060T3

### Motion SPM® 8 Series

### **Features**

- UL Certified No. E209204 (UL1557)
- 600 V 10 A 3-Phase IGBT Inverter Including Control IC for Gate Drive and Protections
- · Low-Loss, Short-Circuit Rated IGBTs
- Separate Open-Emitter Pins from Low-Side IGBTs for Three-Phase Current Sensing
- Active-high interface, works with 3.3 / 5 V Logic, Schmitt-trigger Input
- HVIC for Gate Driving, Under-Voltage, Over Current and Short-Circuit Current Protection
- Fault Output for Under-Voltage, Over Current and Short-Circuit Current Protection
- Inter-Lock Function to Prevent Short-Circuit
- Shut-Down Input
- HVIC Temperature-Sensing Built-In for Temperature Monitoring
- Isolation Rating: 1500 V<sub>rms</sub> / min.

### **Applications**

 Motion Control - Home Appliance / Industrial Motor / HVAC.

### Related Resources

 AN-9112 - Smart Power Module, Motion SPM<sup>®</sup> 8 Series User's Guide.

### **General Description**

FNB81060T3 is a Motion SPM 8 module providing a fully-featured, high-performance inverter output stage for AC Induction, BLDC, and PMSM motors. These modules integrate optimized gate drive of the built-in IGBTs to minimize EMI and losses, while also providing multiple on-module protection features including under-voltage lockouts, inter-lock function, over-current shutdown, thermal monitoring of drive IC, and fault reporting. The built-in, high-speed HVIC requires only a single supply voltage and translates the incoming logic-level gate inputs to the high-voltage, high-current drive signals required to properly drive the module's robust short-circuit-rated IGBTs. Separate negative IGBT terminals are available for each phase to support the widest variety of control algorithms.



SPMFA-A25

Figure 1. 3D Package Drawing (Click to Activate 3D Content)

### **Package Marking and Ordering Information**

Device	Device Marking	Package	Packing Type	Quantity	
FNB81060T3	NB81060T3	SPMFA-A25	RAIL	15	

### **Integrated Power Functions**

• 600 V - 10 A IGBT inverter for three phase DC / AC power conversion (Please refer to Figure 3)

### Integrated Drive, Protection and System Control Functions

- For inverter high-side IGBTs: gate drive circuit, high-voltage isolated high-speed level shifting
   control circuit Under-Voltage Lock-Out (UVLO) protection
   Note: Available bootstrap circuit example is given in Figures 5 and 17
- control circuit Under-Voltage Lock-Out (UVLO) protection
- For inverter low-side IGBTs: gate drive circuit, Over Curent Pretection(OCP), Short-Circuit Protection (SCP) control supply circuit Under-Voltage Lock-Out (UVLO) protection
- Fault signaling: corresponding to UVLO (low-side supply) and SC faults
- Input interface: High-active interface, works with 3.3 / 5 V logic, Schmitt trigger input

### **Pin Configuration**

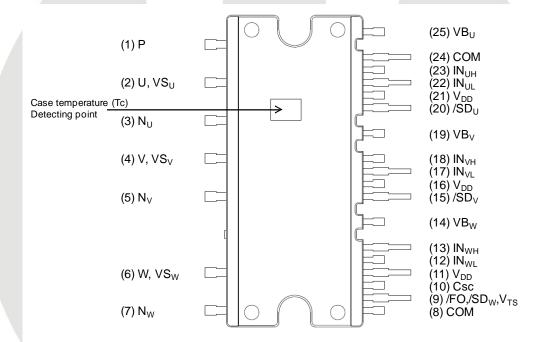


Figure 2. Top View

### **Pin Descriptions**

Pin Number	Pin Name	Pin Description	
1	Р	Positive DC-Link Input	
2	U, VS <sub>U</sub>	Output for U Phase	
3	N <sub>U</sub>	Negative DC-Link Input for U Phase	
4	V, VS <sub>V</sub>	Output for V Phase	
5	N <sub>V</sub>	Negative DC-Link Input for V Phase	
6	W, VS <sub>W</sub>	Output for W Phase	
7	N <sub>W</sub>	Negative DC-Link Input for W Phase	
8	COM	Common Supply Ground	
9	/FO, /SD <sub>W</sub> , V <sub>TS</sub>	Fault Output, Shut-Down Input for W Phase, Temperature Output of Drive IC	
10	C <sub>SC</sub>	Shut Down Input for Over Current and Short Circuit Protection	
11	$V_{DD}$	Common Bias Voltage for IC and IGBTs Driving	
12	IN <sub>WL</sub>	Signal Input for Low-Side W Phase	
13	IN <sub>WH</sub>	Signal Input for High-Side W Phase	
14	VB <sub>W</sub>	High-Side Bias Voltage for W-Phase IGBT Driving	
15	/SD <sub>V</sub>	Shut-Down Input for V Phase	
16	V <sub>DD</sub>	Common Bias Voltage for IC and IGBTs Driving	
17	IN <sub>VL</sub>	Signal Input for Low-Side V Phase	
18	IN <sub>VH</sub>	Signal Input for High-Side V Phase	
19	VB <sub>V</sub>	High-Side Bias Voltage for V-Phase IGBT Driving	
20	/SD <sub>U</sub>	Shut-Down Input for U Phase	
21	V <sub>DD</sub>	Common Bias Voltage for IC and IGBTs Driving	
22	IN <sub>UL</sub>	Signal Input for Low-Side U Phase	
23	IN <sub>UH</sub>	Signal Input for High-Side U Phase	
24	СОМ	Common Supply Ground	
25	VB <sub>U</sub>	High-Side Bias Voltage for U-Phase IGBT Driving	

### **Internal Equivalent Circuit and Input/Output Pins**

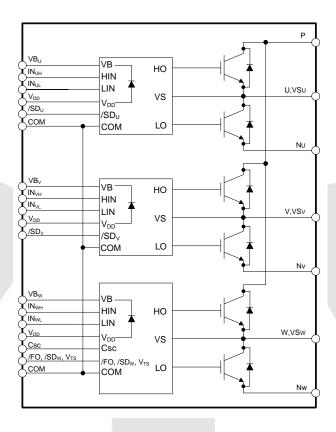


Figure 3. Internal Block Diagram

#### Note:

- 1. Inverter high-side is composed of three IGBTs, freewheeling diodes.
- 2. Inverter low-side is composed of three IGBTs, freewheeling diodes.
- 3. Inverter power side is composed of four inverter DC-link input terminals and three inverter output terminals.

### **Absolute Maximum Ratings** ( $T_J = 25$ °C, unless otherwise specified.)

### **Inverter Part**

Symbol	Parameter	Conditions	Rating	Unit
$V_{PN}$	Supply Voltage	Applied between P - N <sub>U</sub> , N <sub>V</sub> , N <sub>W</sub>	450	V
V <sub>PN(Surge)</sub>	Supply Voltage (Surge)	Applied between P - N <sub>U</sub> , N <sub>V</sub> , N <sub>W</sub>	500	V
V <sub>CES</sub>	Collector - Emitter Voltage		600	V
± I <sub>C</sub>	Each IGBT Collector Current	$T_C = 25^{\circ}C, T_J \le 150^{\circ}C \text{ (Note 4)}$	10	Α
± I <sub>CP</sub>	Each IGBT Collector Current (Peak)	$T_C = 25$ °C, $T_J \le 150$ °C, Under 1 ms Pulse Width (Note 4)	20	А
TJ	Operating Junction Temperature		-40 ~ 150	°C

### **Control Part**

Symbol	Parameter	Conditions	Rating	Unit
V <sub>DD</sub>	Control Supply Voltage	Applied between V <sub>DD</sub> - COM	20	V
V <sub>BS</sub>	High-Side Control Bias Voltage	Applied between $VB_U$ - $VS_U$ , $VB_V$ - $VS_V$ , $VB_W$ - $VS_W$	20	V
V <sub>IN</sub>	Input Signal Voltage	Applied between IN <sub>UH</sub> , IN <sub>VH</sub> , IN <sub>WH</sub> , IN <sub>UL</sub> , IN <sub>VL</sub> , IN <sub>WL</sub> - COM	-0.3 ~ V <sub>DD</sub> +0.3	V
V <sub>FS</sub>	Function Supply Voltage	Applied between /FO, /SD <sub>W</sub> ,V <sub>TS</sub> - COM	-0.3 ~ V <sub>DD</sub> +0.3	V
I <sub>FO</sub>	Fault Current	Sink Current at /FO, /SD <sub>W</sub> ,V <sub>TS</sub> pin	2	mA
V <sub>SC</sub>	Current Sensing Input Voltage	Applied between C <sub>SC</sub> - COM	-0.3 ~ V <sub>DD</sub> +0.3	V

### **Total System**

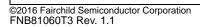
Symbol	Parameter	Conditions	Rating	Unit
V <sub>PN(PROT)</sub>	Self Protection Supply Voltage Limit (Short Circuit Protection Capability)	$V_{DD} = V_{BS} = 13.5 \sim 16.5 \text{ V}, T_{J} = 150^{\circ}\text{C},$ Non-Repetitive, $< 2 \mu\text{s}$	400	V
T <sub>C</sub>	Module Case Operation Temperature	See Figure 2	-40 ~ 125	°C
T <sub>STG</sub>	Storage Temperature		-40 ~ 125	°C
V <sub>ISO</sub>	Isolation Voltage Connect Pins to Heat Sink Plate	AC 60 Hz, Sinusoidal, 1 Minute, Connection Pins to Heat Sink Plate	1500	V <sub>rms</sub>

### **Thermal Resistance**

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
R <sub>th(j-c)Q</sub>	Junction to Case Thermal Resistance	Inverter IGBT part, (Per Module)	-	-	3.40	°C/W
R <sub>th(j-c)F</sub>	(Note 4)	Inverter FWDi part (Per Module)	-	-	3.86	°C / W

### Note:

4. These values had been made an acquisition by the calculation considered to design factor.



### $\textbf{Electrical Characteristics} \ \, (T_J = 25^{\circ}C, \ \, \text{unless otherwise specified.})$

### **Inverter Part**

S	ymbol	Parameter	Cond	itions	Min.	Тур.	Max.	Unit
V	CE(SAT)	Collector - Emitter Saturation Voltage	$V_{IN} = 5 \text{ V}$	T <sub>J</sub> = 25°C	-	1.50	2.10	V
			I <sub>C</sub> = 8 A	T <sub>J</sub> = 150°C	-	1.80	-	V
	$V_{F}$	FWDi Forward Voltage	V <sub>IN</sub> = 0 V	$T_J = 25$ °C	-	1.90	2.50	V
			I <sub>F</sub> = 8 A	T <sub>J</sub> = 150°C	-	1.80	-	٧
HS	t <sub>ON</sub>	Switching Times	$V_{PN} = 400 \text{ V}, V_{DD} = V_{PN}$	<sub>BS</sub> = 15 V, I <sub>C</sub> = 10A	0.25	0.75	1.25	us
	t <sub>C(ON)</sub>		$T_J = 25^{\circ}C$ $V_{IN} = 0 \text{ V} \leftrightarrow 5 \text{ V}, \text{ Indust}$	rtive load	-	0.15	0.45	us
	t <sub>OFF</sub>		(Note 5)	Silve lodd	-	0.50	1.00	us
	t <sub>C(OFF)</sub>				-	0.10	0.40	us
	t <sub>rr</sub>				-	0.10	-	us
LS	t <sub>ON</sub>		$V_{PN} = 400 \text{ V}, V_{DD} = V_{PN}$	<sub>BS</sub> = 15 V, I <sub>C</sub> = 10A	0.25	0.75	1.25	us
	t <sub>C(ON)</sub>		$T_J = 25^{\circ}C$ $V_{IN} = 0 \text{ V} \leftrightarrow 5 \text{ V}, \text{ Indust}$	rtive load	-	0.15	0.45	us
	t <sub>OFF</sub>		(Note 5)	Silve lodd	-	0.50	1.00	us
	t <sub>C(OFF)</sub>				-	0.10	0.40	us
	t <sub>rr</sub>				-	0.10	-	us
	I <sub>CES</sub>	Collector - Emitter Leakage Current	V <sub>CE</sub> = V <sub>CES</sub>		-	-	1.00	mA

<sup>5.</sup>  $t_{ON}$  and  $t_{OFF}$  include the propagation delay of the internal drive IC.  $t_{C(ON)}$  and  $t_{C(OFF)}$  are the switching time of IGBT itself under the given gate driving condition internally. For the detailed information, please see Figure 4.

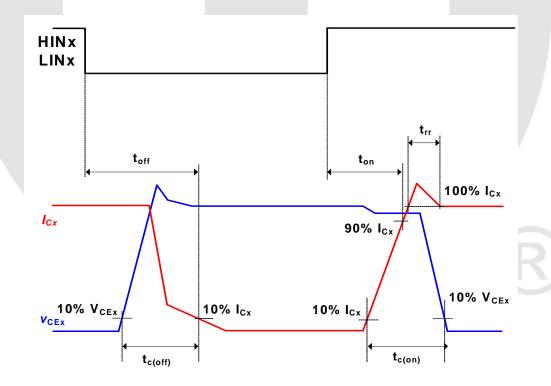


Figure 4. Switching Time Definition

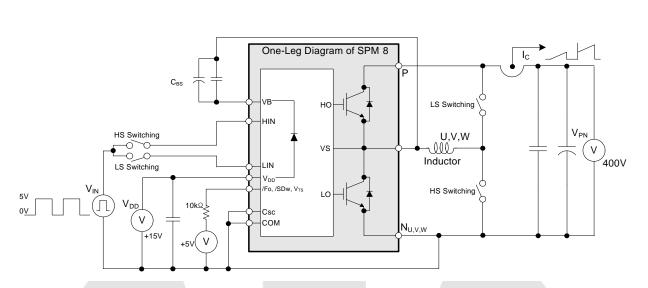


Figure 5. Example Circuit for Switching Test

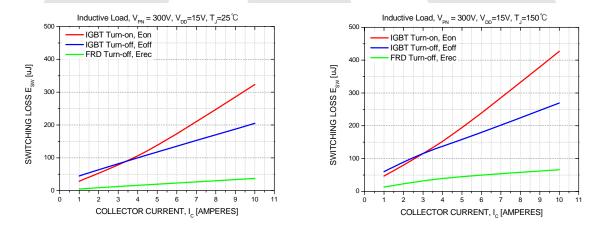


Figure 6. Switching Loss Characteristics

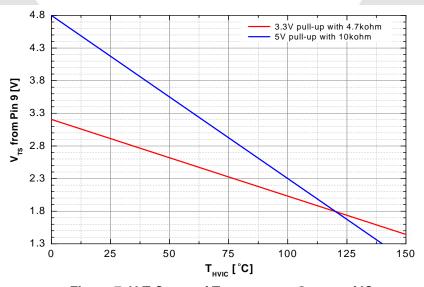


Figure 7. V-T Curve of Temperature Output of IC

### **Control Part**

Symbol	Parameter	Conditions	ľ	Min.	Тур.	Max.	Unit
I <sub>QDD</sub>	Quiescent V <sub>DD</sub> Supply Current	$V_{DD} = 15 \text{ V},$ $IN_{(UH,VH,WH,UL,VL,WL)} = 0 \text{ V}$ $IN_{(UH,VH,WH,UL,VL,WL)} = 0 \text{ V}$	1	-	-	1.7	mA
I <sub>PDD</sub>	Operating V <sub>DD</sub> Supply Current	$V_{DD}$ = 15 V, $f_{PWM}$ = 20 kHz, duty = 50%, applied to one PWM signal input	1	-		2.2	mA
I <sub>QBS</sub>	Quiescent V <sub>BS</sub> Supply Current	$V_{BS} = 15 \text{ V}, \text{IN}_{(UH, VH, WH)} = 0 \text{ V}$ $V_{BU} - V_{SV}$ $V_{SV}$ $V_{SW}$	U	-	-	100	μА
I <sub>PBS</sub>	Operating V <sub>BS</sub> Supply Current	$V_{DD} = V_{BS} = 15 \text{ V, } f_{PWM} = 20 \text{ kHz,}$ $VB_U - VS_V$ duty = 50%, applied to one PWM signal input for high - side		-	-	600	μА
V <sub>FOH</sub>	Fault Output Voltage	$V_{SC}$ = 0 V, /FO Circuit: 10 k $\Omega$ to 5 V Pull-up		3.81	-	-	V
$V_{FOL}$		$V_{SC}$ = 1 V, /FO Circuit: 10 k $\Omega$ to 5 V Pull-up		-	-	0.5	V
V <sub>SC(ref)</sub>	Short-Circuit Trip Level	V <sub>DD</sub> = 15 V (Note 6)		0.46	0.49	0.52	V
UV <sub>DDD</sub>		Detection level		10.0	11.5	13.0	V
$UV_DDR$	Supply Circuit Under-Voltage	Reset level		10.5	12.0	13.5	V
UV <sub>BSD</sub>	Protection	Detection level		9.5	11.0	12.5	V
UV <sub>BSR</sub>		Reset level		10.0	11.5	13.0	V
I <sub>FO_T</sub>	HVIC Temperature	V <sub>DD</sub> = V <sub>BS</sub> = 15 V, T <sub>HVIC</sub> = 25°C		-	82.5	-	μΑ
	Sensing Current	$V_{DD} = V_{BS} = 15 \text{ V}, T_{HVIC} = 75^{\circ}\text{C}$		-	207.5	-	μА
$V_{FO\_T}$	HVIC Temperature	$V_{DD} = V_{BS} = 15 \text{ V}, T_{HVIC} = 25^{\circ}\text{C}, 10 \text{ k}\Omega \text{ to 5 V}$	Pull-up	- \	4.18	-	V
	Sensing Voltage See Figure 7	$V_{DD} = V_{BS} = 15 \text{ V}, T_{HVIC} = 75^{\circ}\text{C}, 10 \text{ k}\Omega \text{ to 5 V}$	Pull-up	-	2.93	-	V
t <sub>FOD</sub>	Fault-Out Pulse Width			40	-	-	μS
V <sub>FSDR</sub>	Shut-down Reset level	Applied between /FO - COM		-	-	2.4	V
V <sub>FSDD</sub>	Shut-down Detection level			8.0	-	-	V
V <sub>IN(ON)</sub>	ON Threshold Voltage	Applied between $IN_{UH}$ , $IN_{VH}$ , $IN_{WH}$ , $IN_{UL}$ , $IN_{V}$	L, IN <sub>WL</sub> -	-	-	2.4	V
V <sub>IN(OFF)</sub>	OFF Threshold Voltage	СОМ		8.0	_	-	V

#### Note:

 $6. \ Short-circuit\ current\ protection\ function\ is\ for\ all\ six\ IGBTs\ if\ the\ /FO,\ /SD_W,\ V_{TS}\ pin\ is\ connected\ to\ /SD_X\ pins.$ 

### **Bootstrap Diode Part**

Symbol	Parameter	Conditions		Тур.	Max.	Unit
R <sub>BS</sub>	Bootstrap Diode Resitance	V <sub>DD</sub> = 15V, T <sub>J</sub> = 25°C	-	280	-	Ω

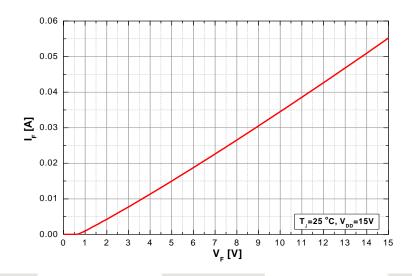


Figure 8. Built-In Bootstrap Diode Charaterstics

### **Recommended Operating Conditions**

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
$V_{PN}$	Supply Voltage	Applied between P - N <sub>U</sub> , N <sub>V</sub> , N <sub>W</sub>	-	300	400	V
$V_{DD}$	Control Supply Voltage	Applied between V <sub>DD</sub> - COM	14.0	15	16.5	V
$V_{BS}$	High - Side Bias Voltage	Applied between $VB_U$ - $VS_U$ , $VB_V$ - $VS_V$ , $VB_W$ - $VS_W$	13.0	15	18.5	V
$dV_{DD}/dt$ , $dV_{BS}/dt$	Control Supply Variation			-	1	V / μs
t <sub>dead</sub>	Blanking Time for Preventing Arm - Short	For each input signal		-	-	μS
V <sub>SEN</sub>	Voltage for Current Sensing	Applied between N <sub>U</sub> , N <sub>V</sub> , N <sub>W</sub> - COM (Including surge voltage)			4	V
P <sub>WIN(ON)</sub>	Minimun Input Pulse	$V_{DD} = V_{BS} = 15 \text{ V}, I_{C} \le 20 \text{ A}, \text{ Wiring Inductance}$	0.7	-		μS
P <sub>WIN(OFF)</sub>	Width	between N <sub>U, V, W</sub> and DC Link N < 10nH (Note 7)	0.7	-	-	

### Note:

7. This product might not make response if input pulse width is less than the recommanded value.

### **Mechanical Characteristics and Ratings**

Parameter	Coi	Min.	Тур.	Max.	Unit	
Device Flatness	See Figure 9		-50	-	100	μm
Mounting Torque	Mounting Screw: - M3	Recommended 0.7 N • m	0.6	0.7	0.8	N • m
	See Figure 10	Recommended 7.1 kg • cm	5.9	6.9	7.9	kg • cm
Weight			-	5.0	-	g

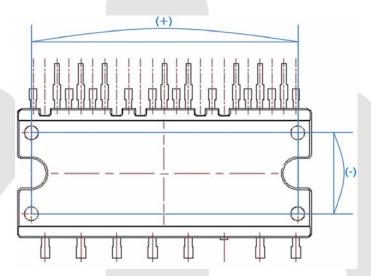


Figure 9. Flatness Measurement Position

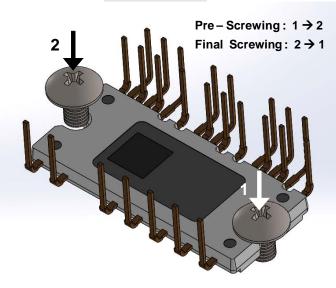


Figure 10. Mounting Screws Torque Order

#### Note:

- 8. Do not make over torque when mounting screws. Much mounting torque may cause package cracks, as well as bolts and AI heat-sink destruction.
- 9. Avoid one side tightening stress. Figure 10 shows the recommended torque order for mounting screws. Uneven mounting can cause of package to be damaged.

  The pre-screwing torque is set to 20 ~ 30 % of maximum torque rating.

### Time Charts of Protective Function

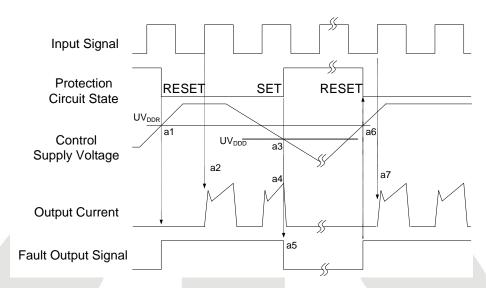


Figure 11. Under-Voltage Protection (Low-Side)

- a1 : Control supply voltage rises: After the voltage rises  $UV_{DDR}$ , the circuits start to operate when next input is applied.
- a2: Normal operation: IGBT ON and carrying current.
- a3 : Under voltage detection (UV<sub>DDD</sub>).
- a4: IGBT OFF in spite of control input condition.
- a5 : Fault output operation starts.
- a6 : Under voltage reset (UV<sub>DDR</sub>).
- a7: Normal operation: IGBT ON and carrying current.

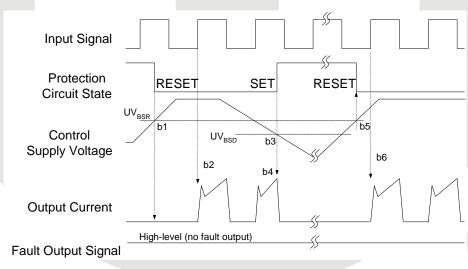


Figure 12. Under-Voltage Protection (High-Side)

- b1 : Control supply voltage rises: After the voltage reaches UV<sub>BSR</sub>, the circuits start to operate when next input is applied.
- b2: Normal operation: IGBT ON and carrying current.
- b3: Under voltage detection (UV<sub>BSD</sub>).
- b4: IGBT OFF in spite of control input condition, but there is no fault output signal.
- b5 : Under voltage reset (UV<sub>BSR</sub>)
- b6: Normal operation: IGBT ON and carrying current

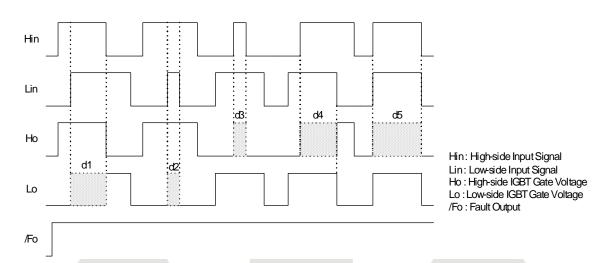


Figure 13. Inter-Lock Function

d1: High Side First - Input - First - Output Mode

d2 : Low Side Noise Mode : No LO d3 : High Side Noise Mode : No HO

d4: Low Side First - Input - First - Output Mode

d5: IN - Phase Mode: No HO

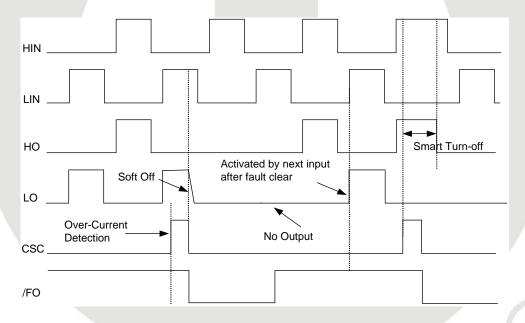


Figure 14. Fault-Out Function By Over Current Protection

HIN: High-side Input Signal LIN: Low-side Input Signal HO: High-Side Output Signal LO: Low-Side Output Signal  $C_{SC}$ : Over Current Detection Input

/FO : Fault Out Function

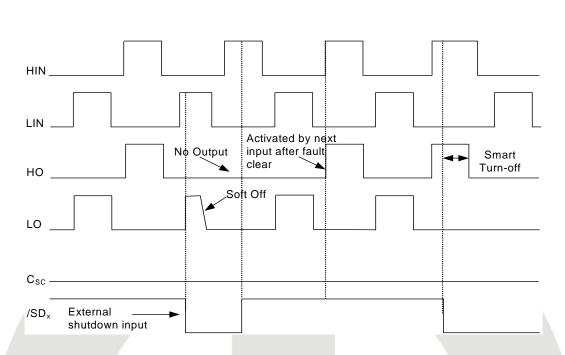


Figure 15. Shutdown Input Function By External Command

$$\begin{split} & \text{HIN}: \text{High-side Input Signal} \\ & \text{LIN}: \text{ Low-side Input Signal} \\ & \text{HO}: \text{ High-Side Output Signal} \\ & \text{LO}: \text{ Low-Side Output Signal} \\ & \text{C}_{\text{SC}}: \text{Over Current Detection Input} \\ & \text{/SD}_{\text{X}}: \text{Shutdown Input Function} \end{split}$$

### Input/Output Interface Circuit

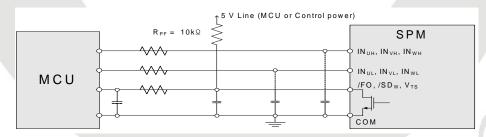
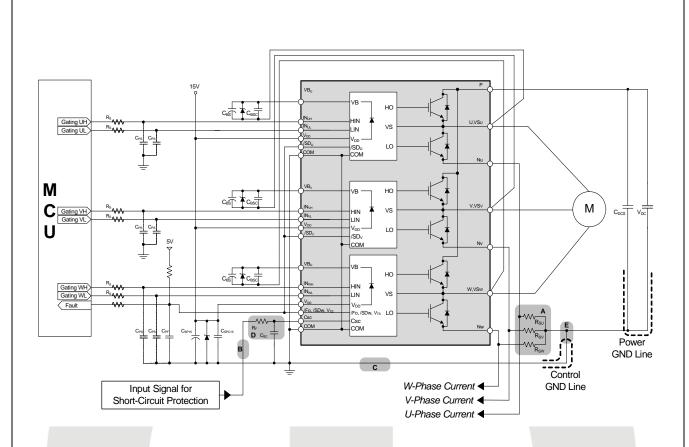


Figure 16. Recommended MCU I/O Interface Circuit

#### Note:

10. RC coupling at each input (parts shown dotted) might change depending on the PWM control scheme used in the application and the wiring impedance of the application's printed circuit board. The input signal section of the SPM 8 product integrates 5 kΩ (typ.) pull-down resistor. Therefore, when using an external filtering resistor, please pay attention to the signal voltage drop at input terminal.

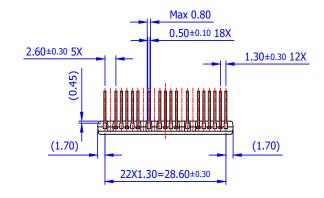


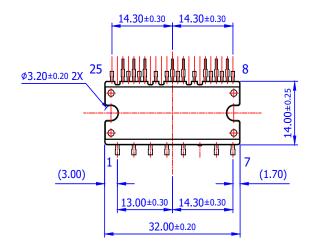
**Figure 17. Typical Application Circuit** 

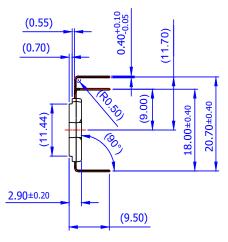
#### Note

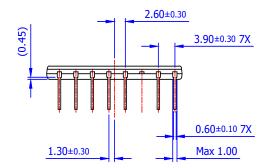
- 11. To avoid malfunction, the wiring of each input should be as short as possible. (less than 2  $\sim$  3 cm)
- 12. /FO is open-drain type. This signal line should be pulled up to the positive side of the MCU or control power supply with a resistor that makes I<sub>FO</sub> up to 1 mA. Please refer to Figure 16.
- 13.  $C_{SP15}$  of around seven times larger than bootstrap capacitor  $C_{BS}$  is recommended.
- 14. Input signal is active-HIGH type. There is a 5 kΩ resistor inside the IC to pull down each input signal line to GND. RC coupling circuits is recommanded for the prevention of input signal oscillation. R<sub>S</sub>C<sub>PS</sub> time constant should be selected in the range 50 ~ 150 ns. (Recommended R<sub>S</sub> = 100 Ω, C<sub>PS</sub> = 1 nF)
- 15. Each wiring pattern inductance of A point should be minimized (Recommend less than 10nH). Use the shunt resistor R<sub>S(UV/VM)</sub> of surface mounted (SMD) type to reduce wiring inductance. To prevent malfunction, wiring of point E should be connected to the terminal of the shunt resistor R<sub>S(UV/VM)</sub> as close as possible.
- 16. To prevent errors of the protection function, the wiring of B, C, and D point should be as short as possible.
- 17. In the short-circuit protection circuit, please select the R<sub>F</sub>C<sub>SC</sub> time constant in the range 1.5 ~ 2 μs. Do enough evaluation on the real system because short-circuit protection time may very wiring pattern layout and value of the R<sub>F</sub> and C<sub>SC</sub> time constant.
- 18. The connection between control GND line and power GND line which includes the N<sub>U</sub>, N<sub>V</sub>, N<sub>W</sub> must be connected to only one point. Please do not connect the control GND to the power GND by the broad pattern. Also, the wiring distance between control GND and power GND should be as short as possible.
- 19. Each capacitor should be mounted as close to the pins of the Motion SPM 8 product as possible.
- 20. To prevent surge destruction, the wiring between the smoothing capacitor and the P and GND pins should be as short as possible. The use of a high frequency non-inductive capacitor of around 0.1 ~ 0.22 μF between the P and GND pins is recommended.
- 21. Relays are used at almost every systems of electrical equipments of home appliances. In these cases, there should be sufficient distance between the CPU and the relays.
- 22. The zener diode or transient voltage suppressor should be adopted for the protection of ICs from the surge destruction between each pair of control supply terminals. (Recommanded zener diode is 22 V / 1 W, which has the lower zener impedance characteristic than about 15 Q)
- 23. Please choose the electrolytic capacitor with good temperature characteristic in C<sub>BS</sub>. Also, choose 0.1 ~ 0.2 µF R-category ceramic capacitors with good temperature and frequency characteristics in C<sub>BSC</sub>.
- 24. For the detailed information, please refer to the application notes.
- 25. /FO and /SD must be connected as short as possible.

### Detailed Package Outline Drawings (FNB81060T3, Long Lead)









NOTES: UNLESS OTHERWISE SPECIFIED

- A) NO PACKAGING STANDARD APPLIES
- B) ALL DIMENSIONS ARE IN MILLIMETERS
- C) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS
- D) ( ) IS REFERENCE
- E) DRAWING FILENAME: MOD25DAREV2



Package drawings are provided as a service to customers considering Fairchild components. Drawings may change in any manner without notice. Please note the revision and/or data on the drawing and contact a FairchildSemiconductor representative to verify or obtain the most recent revision. Package specifications do not expand the terms of Fairchild's worldwide therm and conditions, specifically the the warranty therein, which covers Fairchild products.

Always visit Fairchild Semiconductor's online packaging area for the most recent package drawings:

http://www.fairchildsemi.com/dwg/MO/MOD25DA.pdf



#### TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

AccuPower™ F-PES™ FRFET® AttitudeEngine™

Global Power Resource SM Awinda<sup>®</sup> AX-CAP®\* GreenBridge™ BitSiC™ Green FPS™ Build it Now™ Green FPS™ e-Series™

CorePLUS™ Gmax™ CorePOWER™ GTO™ CROSSVOLT™ IntelliMAX™ ISOPLANAR™

Current Transfer Logic™ Making Small Speakers Sound Louder

DEUXPEED<sup>®</sup> and Better™ Dual Cool™ MegaBuck™ EcoSPARK® MICROCOUPLER™ EfficientMax™ MicroFET™ ESBC™ MicroPak™

MicroPak2™ MillerDrive™ Fairchild<sup>®</sup> MotionMax™ Fairchild Semiconductor® MotionGrid<sup>®</sup>

FACT Quiet Series™ FastvCore™

FETBench™ EPS\*

MTi<sup>®</sup> MTx® MVN® mWSaver® OptoHiT™ OPTOLOGIC® OPTOPLANAR®

(E)

PowerTrench<sup>1</sup>

Power Supply WebDesigner™

PowerXS<sup>™</sup>

Programmable Active Droop™

OFFT QSTM Quiet Series™ RapidConfigure™

Saving our world, 1mW/W/kW at a time™

SignalWise™ SmartMax™ SMART START™

Solutions for Your Success™

SPM® STEALTH™ SuperFET® SuperSOT™-3 SuperSOT™-6 SuperSOT™-8 SupreMOS<sup>®</sup>

SyncFET™ Sync-Lock™

SYSTEM GENERAL®

TinyBoost® TinyBuck TinyCalc™ TinyLogic<sup>®</sup> TINYOPTO™ TinyPower™ TinyPWM™ TinyWire™ Tran SiC™ TriFault Detect™ TRUECURRENT®\* u.SerDes™

UHC<sup>®</sup> Ultra FRFET™ UniFET™ VCX™ VisualMax™ VoltagePlus™ XSTM

Xsens™ 仙童®

\* Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. TO OBTAIN THE LATEST, MOST UP-TO-DATE DATASHEET AND PRODUCT INFORMATION, VISIT OUR WEBSITE AT <a href="http://www.fairchildsemi.com">http://www.fairchildsemi.com</a>, FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

#### **AUTHORIZED USE**

Unless otherwise specified in this data sheet, this product is a standard commercial product and is not intended for use in applications that require extraordinary levels of quality and reliability. This product may not be used in the following applications, unless specifically approved in writing by a Fairchild officer: (1) automotive or other transportation, (2) military/aerospace, (3) any safety critical application – including life critical medical equipment – where the failure of the Fairchild product reasonably would be expected to result in personal injury, death or property damage. Customer's use of this product is subject to agreement of this Authorized Use policy. In the event of an unauthorized use of Fairchild's product, Fairchild accepts no liability in the event of product failure. In other respects, this product shall be subject to Fairchild's Worldwide Terms and Conditions of Sale, unless a separate agreement has been signed by both Parties.

### ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.fairchildsemi.com,

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufacturers of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed applications, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handling and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address any warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

#### PRODUCT STATUS DEFINITIONS

#### **Definition of Terms**

Demination of Terms		
Datasheet Identification Product Status		Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

Rev. 177

ON Semiconductor and in are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at <a href="www.onsemi.com/site/pdt/Patent-Marking.pdf">www.onsemi.com/site/pdt/Patent-Marking.pdf</a>. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and exp

### **PUBLICATION ORDERING INFORMATION**

#### LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800-282-9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

# **Mouser Electronics**

**Authorized Distributor** 

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

ON Semiconductor:

FNB81060T3